EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	230	aluminum near dop$3 near (semiconductor or polysilicon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/08/05 11:47
L5	2	("20040126914").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2011/08/05 12:25
S2	660	257/e29.117.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/01 14:37
S3	2	257/e29.145.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/01 14:37
S4	34	("4591848" | "5132819" | "5457474" | "5477073" | "5567959" | "5644147" | "5807772" | "5814834" | "5818070" | "5821137" | "5834797" | "5917199" | "5917221" | "5929527" | "5956011" | "6010923" | "6037924" | "6072193" | "6081131" | "6150283" | "6153893" | "6197624" | "6198133" | "6204519" | "6207971" | "6215154" | "6380011" | "6392628" | "6396078" | "6462723" | "6512271" | "6569716" | "6603453" | "6608613").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/05/01 14:38

S6	40	(light near shield) same (titanium near oxide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/02 11:39
S7	2	("20020089616").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 11:46
S10	2	("20010034088").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/02 16:36
S11	212	("thin film transistor" or tft) same ((liquid near crystal) near (electroluminescent or el))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/05 10:16
S12	3824	257/347.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/05 10:54
S13	26	capacitor near electrode near copper	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/06 14:14
S14	13	((("20030143794") or ("6787407") or ("20010034088") or ("6821827") or ("20050054181") or ("20030219934") or ("6908796") or ("20020089616") or ("6587165")).PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/06 14:56
S15	376	257/e27.116.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 11:37

S16	3566	((SHUNPEI) near2 (YAMAZAKI)).INV.	US-PGPUB; USPAT	OR	ON	2008/11/03 11:41
S17	338	((SHUNPEI) near2 (YAMAZAKI)).INV. and ("droplet discharge" or "ink-jet")	US-PGPUB; USPAT	OR	ON	2008/11/03 11:42
S18	13	(("20070132377") or ("20070082443") or ("20070040971") or ("20070096096") or ("7176069") or ("7202497") or ("7192865")).PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/03 11:47
S19	8	(("5948705") or ("6221140") or ("6043149") or ("5706064")).PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/03 11:53
S20	2	"US 20070085938"	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2008/11/03 12:18
S21	7	("4712874" | "5153753" | "5321535" | "5321538" | "5503932" | "5517343" | "5520855").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/11/03 12:37
S22	16	(("20020089616") or ("6365917") or ("5706064") or ("4389481") or ("5329390") or ("20010034088") or ("20010014528") or ("6461914")).PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/03 17:16
S23	2	"US 20070085938"	US-PGPUB; USPAT; USOCR; DERWENT	OR	ON	2008/11/03 19:07
S25	85	(copper near wiring) same (tft or "thin film transistor")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 19:22
S26	81	(amorphous near gate) same (tft or "thin film transistor")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 19:50

S27	4003	257/347.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 20:18
S28	733	257/e29.117.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 20:19
S29	1461	257/e29.137.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 20:19
S30	950	257/e29.273.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 20:19
S31	203	257/e29.202.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 20:19
S32	3	257/e29.145.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 20:19
S33	944	257/e29.147.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 20:19
S34	212	257/e31.096.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 20:20

S35	1699	257/e33.061.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 20:20
S36	365	257/e31.095.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/11/03 20:20
S37	458	("thin film transistor" or tft) same ((liquid near crystal or LCD) near (electroluminescent or el))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/15 18:39
S41	15	("thin film transistor" or tft) same (liquid near crystal or LCD) same (electroluminescent or el) same (insulat$3 or dielectric) with (opening or recess or window or via or throughhole or trench)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/15 18:41
S42	36	("thin film transistor" or tft) near (liquid near crystal or LCD) near (electroluminescent or el)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/15 18:44
S43	198	("thin film transistor" or tft) same (liquid near crystal or LCD) same (electroluminescent or el) same (insulat$3 or dielectric) with (metal or interconnect or conduct$3 or via or plug)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 17:24
S44	251	("thin film transistor" or tft) same (liquid near crystal or LCD) same (electroluminescent or el) same (insulat$3 or dielectric) same (metal or interconnect or conduct$3 or via or plug)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 17:25

S45	4207	257/347.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 21:03
S46	808	257/e29.117.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 21:03
S47	1584	257/e29.137.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 21:03
S48	1024	257/e29.273.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 21:03
S49	217	257/e29.202.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 21:03
S50	3	257/e29.145.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 21:03
S51	1025	257/e29.147.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 21:03
S52	218	257/e31.096.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 21:03

S53	215	257/e33.061.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 21:04
S54	392	257/e31.095.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 21:04
S55	45	planariz$5 near metal near plug	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 19:07
S56	4375	257/347.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 19:29
S57	826	257/e29.117.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 19:29
S58	1593	257/e29.137.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 19:29
S59	1124	257/e29.273.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 19:30
S60	220	257/e29.202.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 19:30

S61	3	257/e29.145.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 19:30
S62	1029	257/e29.147.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 19:30
S63	221	257/e31.096.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 19:30
S64	279	257/e33.061.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 19:30
S65	402	257/e31.095.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/10/29 19:31
S66	18	"alkyl cyanobiphenyl"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/10 15:09
S67	1	((triphenylamine near derivative) or "MTDATA") near insulat$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/10 15:23
S68	1	((diamine near derivative) or (TPD)) near insulat$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/02/10 15:27

S69	2	("6211067").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2010/02/10 16:05
S70	108	(luminesc$4 near insulat $3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/28 18:12
S71	658	257/349.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/28 20:20
S72	853	257/e29.117.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/28 20:20
S73	445	("thin film transistor" or tft) same (insulat$3 or dielectric) same (metal or interconnect or conduct$3 or via or plug) same lithograph$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/12/21 13:41
S74	332	("thin film transistor" or tft) same (liquid near crystal or LCD) same (electroluminescent or el) same (insulat$3 or dielectric) same (metal or interconnect or conduct$3 or via or plug)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/12/21 13:42
S75	443	S73 not S74	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/12/21 13:42
S76	680	257/349.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/12/21 15:38

S77	876	257/e29.117.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/12/21 15:38
S78	4845	257/347.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/12/23 13:09
S80	632	((impurity near region) or (dop$3 near region) or source or drain) near metal $3 near (silver or ag or platinum or pt or tungsten or gold or iridium or rhodium or aluminum or zinc or zn or cadmium or zirconium or barium or indium)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/07/25 12:20
S81	7	((impurity near region) or (dop$3 near region)) near metal$3 near (silver or ag or platinum or pt or tungsten or gold or iridium or rhodium or aluminum or zinc or zn or cadmium or zirconium or barium or indium)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/07/25 12:22
S82	81	((impurity near region) or (dop$3 near region)) with (metal$3 near (silver or ag or platinum or pt or tungsten or gold or iridium or rhodium or aluminum or zinc or zn or cadmium or zirconium or barium or indium))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/07/25 12:40
S83	122	(semiconductor near dop $3) near (gold or silver or platinum or aluminum)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/07/25 12:50
S84	59	gold near dop$3 near (semiconductor or polysilicon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/07/25 14:33

EAST Search History (Interference)

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8/5/2011 12:30:22 PM
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